Quad 2-Input NAND Gate with Schmitt-Trigger Inputs with LSTTL Compatible Inputs

High-Performance Silicon-Gate CMOS

The MC74HCT132A is identical in pinout to the LS132. The device inputs are compatible with standard CMOS outputs; with pull-up resistors, they are compatible with LSTTL outputs.

The MC74HCT132A can be used to enhance noise immunity or to square up slowly changing waveforms.

Features

- Output Drive Capability: 10 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 2.0 to 6.0 V
- Low Input Current: 1.0 μA
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance with the Requirements as Defined by JEDEC Standard No. 7A
- Chip Complexity: 72 FETs or 18 Equivalent Gates
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

A1 [1 ●	14] v _{cc}] в4
B1 [2	13	В4
Y1 [3	12	A4
A2 [4	11	Y4
B2 [5	10	В3
Y2 [6	9	_ A3
GND [7	8	Y3
			•

Figure 1. Pin Assignment



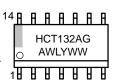
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MARKING DIAGRAMS



SOIC-14 D SUFFIX CASE 751A





TSSOP-14 DT SUFFIX CASE 948G



= Assembly Location

WL, L = Wafer Lot

′ = Year

WW, W = Work Week

G or ■ = Pb-Free Package

(Note: Microdot may be in either location)

FUNCTION TABLE

Inp	uts	Output
Α	В	Y
L	L	Н
L	Н	Н
Н	L	Н
н	Н	L

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

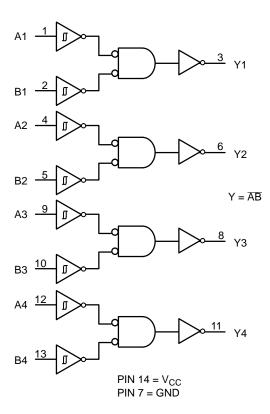


Figure 2. Logic Diagram

ORDERING INFORMATION

Device	Package	Shipping [†]
MC74HCT132ADG		55 Units / Rail
MC74HCT132ADR2G	SOIC-14 (Pb-Free)	2500 / Tape & Reel
NLV74HCT132ADR2G*	(121100)	2500 / Tape & Reel
MC74HCT132ADTR2G	TSSOP-14	2500 / Tape & Reel
NLVHCT132ADTR2G*	(Pb-Free)	2500 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{*}NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable.

MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	Positive DC Supply Voltage	-0.5 to +7.0	V
V _{IN}	Digital Input Voltage	-0.5 to +7.0	V
V _{OUT}	DC Output Voltage Output in 3-State High or Low State	-0.5 to +7.0 -0.5 to V _{CC} +0.5	V
I _{IK}	Input Diode Current	-20	mA
I _{OK}	Output Diode Current	±20	mA
I _{OUT}	DC Output Current, per Pin	± 25	mA
I _{CC}	DC Supply Current, V _{CC} and GND Pins	±75	mA
I _{GND}	DC Ground Current per Ground Pin	±75	mA
T _{STG}	Storage Temperature Range	-65 to +150	°C
T _L	Lead Temperature, 1 mm from Case for 10 Seconds	260	°C
TJ	Junction Temperature Under Bias	+150	°C
θ_{JA}	Thermal Resistance 14–SOIC 14–TSSOP	125 170	°C/W
P _D	Power Dissipation in Still Air at 85°C SOIC TSSOP	500 450	mW
MSL	Moisture Sensitivity	Level 1	
F _R	Flammability Rating Oxygen Index: 30% – 35%	UL 94 V0 @ 0.125 in	
V _{ESD}	ESD Withstand Voltage Human Body Model (Note 1) Machine Model (Note 2) Charged Device Model (Note 3)	> 2000 > 100 > 500	V
I _{Latch-Up}	Latch-Up Performance Above V _{CC} and Below GND at 85°C (Note 4)	±300	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. Tested to EIA/JESD22-A114-A.
- 2. Tested to EIA/JESD22-A115-A.
- 3. Tested to JESD22-C101-A.
- 4. Tested to EIA/JESD78.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V _{CC}	DC Supply Voltage (Referenced to GND)	2.0	6.0	V
V _{IN} , V _{OUT}	DC Input Voltage, Output Voltage (Referenced to GND)	0	V _{CC}	V
T _A	Operating Temperature, All Package Types	- 55	+125	°C
t _r , t _f	Input Rise and Fall Time (Figure 3)	_	No Limit (Note 5)	ns

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

- 5. When V_{IN} ~ 0.5 V_{CC}, I_{CC} >> quiescent current.
 6. Unused inputs may not be left open. All inputs must be tied to a high–logic voltage level or a low–logic input voltage level.

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

			V _{CC}	Guarar	nteed Limit		
Symbol	Parameter	Test Conditions	٧	−55°C to 25°C	≤85°C	≤125°C	Unit
V _{T+} max	Maximum Positive–Going Input Threshold Voltage	$V_{OUT} = 0.1 \text{ V}$ $ I_{OUT} \le 20 \mu\text{A}$	4.5 5.5	1.9 2.1	1.9 2.1	1.9 2.1	V
V _{T+} min	Minimum Positive–Going Input Threshold Voltage	$V_{OUT} = 0.1 \text{ V}$ $ I_{OUT} \le 20 \mu\text{A}$	4.5 5.5	1.2 1.4	1.2 1.4	1.2 1.4	V
V _T _max	Maximum Negative-Going Input Threshold Voltage	$V_{OUT} = V_{CC} - 0.1 \text{ V}$ $ I_{OUT} \le 20 \mu\text{A}$	4.5 5.5	1.2 1.4	1.2 1.4	1.2 1.4	V
V _T _min	Minimum Negative–Going Input Threshold Voltage	$V_{OUT} = V_{CC} - 0.1 \text{ V}$ $ I_{OUT} \le 20 \mu\text{A}$	4.5 5.5	0.5 0.6	0.5 0.6	0.5 0.6	V
V _H min (Note 7)	Minimum Hysteresis Voltage	$V_{OUT} = 0.1 \text{ V or } V_{CC} - 0.1 \text{ V}$ $ I_{OUT} \le 20 \mu\text{A}$	4.5 5.5	0.4 0.4	0.4 0.4	0.4 0.4	V
V _{OH}	Minimum High-Level Output Voltage	$V_{IN} \le V_{T-}$ min or V_{T+} max $ I_{OUT} \le 20 \mu A$	4.5 5.5	4.4 5.4	4.4 5.4	4.4 5.4	V
		$V_{IN} \le -V_{T}$ min or V_{T_+} max $ I_{OUT} \le 4.0 \text{ mA}$	4.5	3.98	3.84	3.7	
V_{OL}	Maximum Low-Level Output Voltage	$V_{IN} \ge V_{T+} max$ $ I_{OUT} \le 20 \mu A$	4.5 5.5	0.1 0.1	0.1 0.1	0.1 0.1	٧
		$V_{IN} \ge V_{T+} max$ $ I_{OUT} \le 4.0 mA$	4.5	0.26	0.33	0.4	
I _{IN}	Maximum Input Leakage Current	V _{IN} = V _{CC} or GND	5.5	±0.1	±1.0	±1.0	μΑ
I _{CC}	Maximum Quiescent Supply Current (per Package)	$V_{IN} = V_{CC}$ or GND $I_{OUT} = 0 \mu A$	5.5	1.0	10	40	μΑ

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

7. $V_{H}min > (V_{T}min) - (V_{T}max)$; $V_{H}max = (V_{T}max) + (V_{T}min)$.

AC ELECTRICAL CHARACTERISTICS (C_L = 50 pF, Input t_f = t_f = 6.0 ns, V_{CC} = 5.0 V \pm 10%)

		V _{CC}	Guaranteed Limit			
Symbol	Parameter	V	−55°C to 25°C	≤85°C	≤125°C	Unit
t _{PLH} , t _{PHL}	Maximum Propagation Delay, Input A or B to Output Y (Figures 3 and 4)	5.0	25	31	38	ns
t _{TLH} , t _{THL}	Maximum Output Transition Time, Any Output (Figures 3 and 4)	5.0	15	19	22	ns
C _{in}	Maximum Input Capacitance	_	10	10	10	pF

		Typical @ 25°C, V _{CC} = 5.0 V	
C_{PD}	Power Dissipation Capacitance (per Gate) (Note 8)	24	рF

^{8.} Used to determine the no–load dynamic power consumption: $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$.

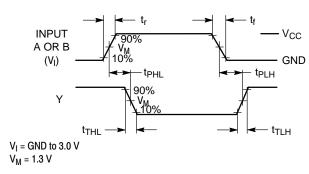
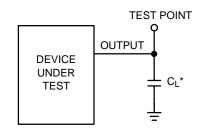


Figure 3. Switching Waveforms



*Includes all probe and jig capacitance

Figure 4. Test Circuit

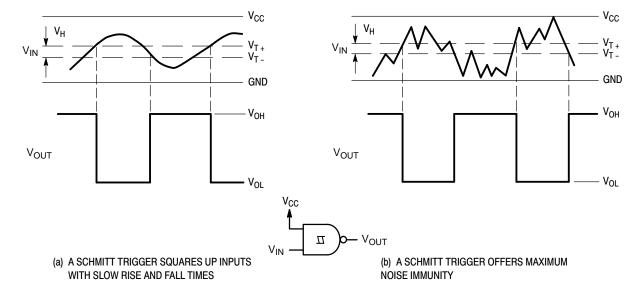


Figure 5. Typical Schmitt-Trigger Applications

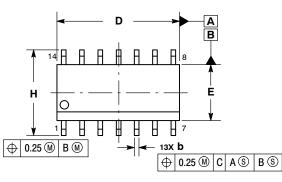


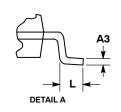


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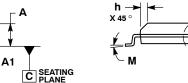
SOIC-14 NB CASE 751A-03 ISSUE L

DATE 03 FEB 2016





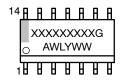




- NOTES:
 1. DIMENSIONING AND TOLERANCING PER
 - ASME Y14.5M, 1994.
 CONTROLLING DIMENSION: MILLIMETERS.
- DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF AT
- MAXIMUM MATERIAL CONDITION.
 DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSIONS.
- 5. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE

	MILLIMETERS		MILLIMETERS INCHES		HES
DIM	MIN MAX		MIN	MAX	
Α	1.35	1.75	0.054	0.068	
A1	0.10	0.25	0.004	0.010	
АЗ	0.19	0.25	0.008	0.010	
b	0.35	0.49	0.014	0.019	
D	8.55	8.75	0.337	0.344	
Е	3.80	4.00	0.150	0.157	
е	1.27	1.27 BSC		BSC	
Н	5.80	6.20	0.228	0.244	
h	0.25	0.50	0.010	0.019	
L	0.40	1.25	0.016	0.049	
M	0 °	7°	0 °	7°	

GENERIC MARKING DIAGRAM*

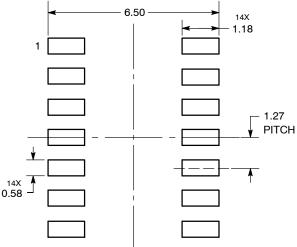


XXXXX = Specific Device Code Α = Assembly Location

WL = Wafer Lot Υ = Year WW = Work Week = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

SOLDERING FOOTPRINT* - 6.50 -



DIMENSIONS: MILLIMETERS *For additional information on our Pb-Free strategy and soldering

details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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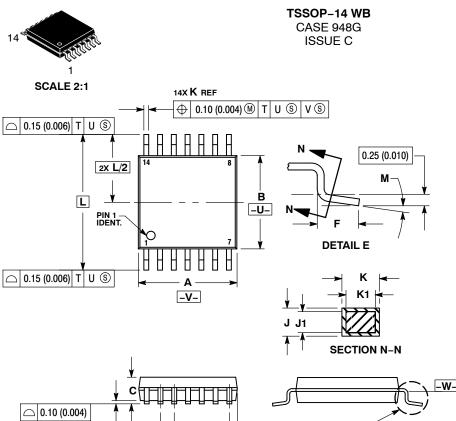
SOIC-14 CASE 751A-03 ISSUE L

DATE 03 FEB 2016

STYLE 1: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. NO CONNECTION 5. ANODE/CATHODE 6. NO CONNECTION 7. ANODE/CATHODE 8. ANODE/CATHODE 9. ANODE/CATHODE 10. NO CONNECTION 11. ANODE/CATHODE 12. ANODE/CATHODE 13. NO CONNECTION 14. COMMON ANODE	STYLE 2: CANCELLED	STYLE 3: PIN 1. NO CONNECTION 2. ANODE 3. ANODE 4. NO CONNECTION 5. ANODE 6. NO CONNECTION 7. ANODE 8. ANODE 9. ANODE 10. NO CONNECTION 11. ANODE 12. ANODE 13. NO CONNECTION 14. COMMON CATHODE	STYLE 4: PIN 1. NO CONNECTION 2. CATHODE 3. CATHODE 4. NO CONNECTION 5. CATHODE 6. NO CONNECTION 7. CATHODE 8. CATHODE 9. CATHODE 10. NO CONNECTION 11. CATHODE 12. CATHODE 13. NO CONNECTION 14. COMMON ANODE
STYLE 5: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. ANODE/CATHODE 5. ANODE/CATHODE 6. NO CONNECTION 7. COMMON ANODE 8. COMMON CATHODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. ANODE/CATHODE 12. ANODE/CATHODE 13. NO CONNECTION 14. COMMON ANODE	STYLE 6: PIN 1. CATHODE 2. CATHODE 3. CATHODE 4. CATHODE 5. CATHODE 6. CATHODE 7. CATHODE 8. ANODE 9. ANODE 10. ANODE 11. ANODE 12. ANODE 13. ANODE 14. ANODE	STYLE 7: PIN 1. ANODE/CATHODE 2. COMMON ANODE 3. COMMON CATHODE 4. ANODE/CATHODE 5. ANODE/CATHODE 6. ANODE/CATHODE 7. ANODE/CATHODE 8. ANODE/CATHODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. COMMON CATHODE 12. COMMON ANODE 13. ANODE/CATHODE 14. ANODE/CATHODE	STYLE 8: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. NO CONNECTION 5. ANODE/CATHODE 6. ANODE/CATHODE 7. COMMON ANODE 8. COMMON ANODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. NO CONNECTION 12. ANODE/CATHODE 13. ANODE/CATHODE 14. COMMON CATHODE

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DATE 17 FEB 2016

- NOTES.

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: MILLIMETER.

 3. DIMENSION A DOES NOT INCLUDE MOLD
- FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
 DIMENSION B DOES NOT INCLUDE
- INTERLEAD FLASH OR PROTRUSION.
 INTERLEAD FLASH OR PROTRUSION SHALL
- INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.

 DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.

 TERMINAL NUMBERS ARE SHOWN FOR DEEEDENIC OMITY.
- REFERENCE ONLY.
 DIMENSION A AND B ARE TO BE
- DETERMINED AT DATUM PLANE -W-.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	4.90	5.10	0.193	0.200
В	4.30	4.50	0.169	0.177
С		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
Н	0.50	0.60	0.020	0.024
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
М	o°	8 °	0 °	8 °

GENERIC MARKING DIAGRAM*



= Assembly Location

= Wafer Lot V = Year

W = Work Week

= Pb-Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

0.10 (0.004) -T- SEATING PLANE	H DETAIL E
SOLDERING	FOOTPRINT
7. 1 1 1 14X 0.36	0.65 PITCH

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